

Influence of different nano titania on microstructure and electrical properties of low voltage zinc oxide varistors

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Abstract A series of check experiments showed that ZnO varistors doped with TiO₂ of different particle sizes and dispersing states have different densities, porosities and grain morphologies, which relate to their electrical properties tightly. Compared with samples added with TiO₂ dopants of others types, the varistors added with nm-TiO₂ sol exhibit large density, low porosity, big granular size, low breakdown voltage gradient and small leakage current. Hence nm-TiO₂ sol dopant is the best grain growth enhancing additive for optimizing almost all the electrical parameters.

Keywords Porosity · Dispersing state · Electrical properties · Morphology · Voltage gradient

1 Introduction

ZnO varistors, which are ceramic semiconductor devices with highly nonlinear current/voltage characteristics, have been proved [1] to be of excellent properties in surge protection against transient overvoltage in electronic circuitry. They are produced by sintering ZnO powder

together with small amount of other metal oxides such as Bi₂O₃, Sb₂O₃ and TiO₂.

The mechanism of conduction and the influence of additives in varistors have been investigated by many workers [2–5], nevertheless most of their results were drawn from varistor samples based on ZnO–Bi₂O₃–Sb₂O₃ system ceramic with high breakdown voltage. The studies of ZnO–Bi₂O₃–TiO₂ system based varistor with low breakdown voltage are still inadequate so far.

H. Suzuki and R.C. Bradt [6] attributed the low breakdown voltage to the large grain size in ZnO–Bi₂O₃–TiO₂ system ceramic compared with that of ZnO–Bi₂O₃–Sb₂O₃ system. They also suggested that TiO₂ enhances the growth of ZnO grains by replacement diffusion of Ti cations on the surface of grains.

In this paper, three types of TiO₂ additives-micron-sized (5–10 μm) TiO₂ powder, nano-sized (20 nm on average) TiO₂ powder and nano-sized TiO₂ sol (19 nm on average), were used in the experiment. The influence of TiO₂ of different particle sizes and dispersing states on low voltage varistors were systematically studied for complementing previous pertinent studies.

2 Experimental

For 2 h 98.3 mol% ZnO, 0.7 mol% Bi₂O₃ and 1.0 mol% TiO₂ were ball milled with zirconia balls and deionised water. The mixtures were then dried and pressed into discs of 17-mm and 2-mm thickness. The samples were sintered at 900, 1000, 1100, 1200 °C for 2 h, respectively.

For electrical measurements, the sintered samples were coated with conductive silver paint on both surfaces, then

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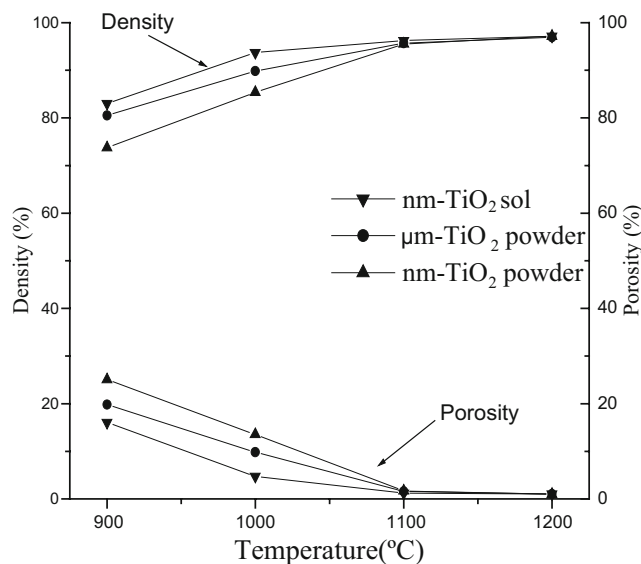


Fig. 1 Variation of density with sintering temperature

heat cured to provide ohmic contacts. I - V characteristics were determined using CJ1001 semiconductor testing device at room temperature. Rough polished by 400#–1200# grit SiC papers and Cr₂O₃ powders, samples were etched by acetic acid for 10 min for SEM analysis.

3 Results and discussion

3.1 Microstructure

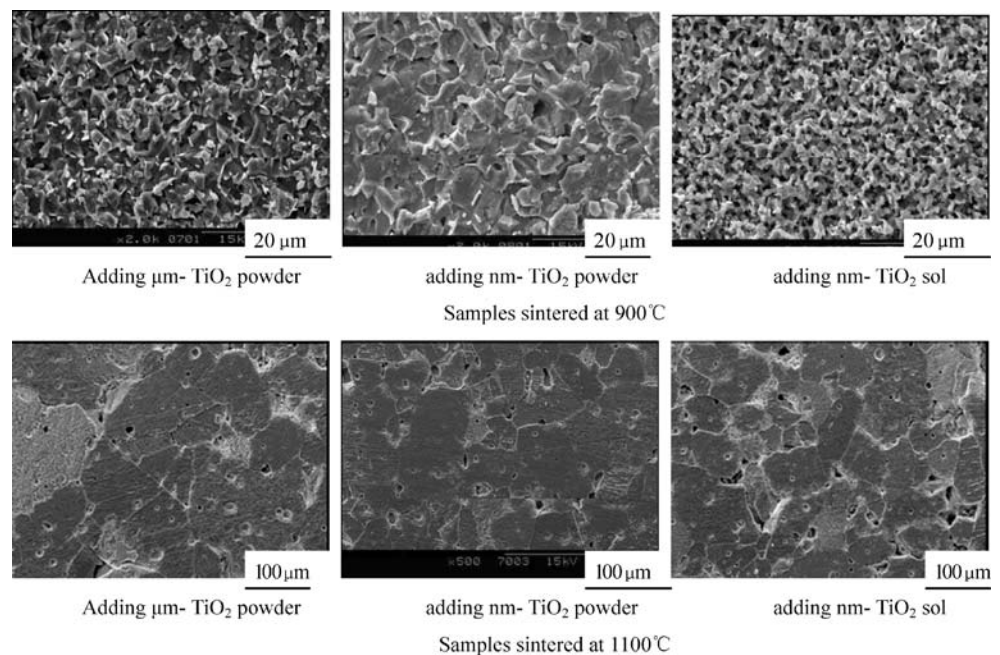
The curves of density and porosity are showed in Fig. 1. As shown, the difference in dispersing states of TiO₂ powders

results in difference in density and porosity of samples. Below 1100 °C, the samples containing nm-TiO₂ sol exhibited the largest density and the lowest porosity. At the same temperature, the samples with nm-TiO₂ powder exhibited the lowest density, even lower than the samples with μm-TiO₂ powder apparently. From curves of porosity, the highest porosity of samples with nm-TiO₂ powder means a considerable amount of pores occurred while nm-TiO₂ powder agglomeration shrinking.

As SEM photos shown (see Fig. 2), the comparison of diameter of grains in each sample (measured by Mendelson method [7], as described in Fig. 3) shows that samples with nm-TiO₂ powder had smaller grains than samples with nm-TiO₂ sol. It should be noted that at 900 °C, different from other two samples, the grains of samples added nm-TiO₂ sol combined together without clear grain boundaries. Such phenomenon only occur in binary ZnO–TiO₂ system without Bi₂O₃, for Bi congregates at the grain boundary, separating the grains and forms Bi-rich grain boundaries [8].

Existing in forms of monodispersing nm-particles, nm-TiO₂ sol with large specific area and high mobility of surface atoms promotes grain rearrangement and mass transfer among grains, accelerates pyknosis of ceramics as well as lowers down porosity and enhances grain growth to the best advantage; different from nm-TiO₂ sol, nm-TiO₂ powder exists in forms of agglomerates with thermodynamic instability, whose size is even larger than μm-TiO₂ powder. The aggregating particles tend to shrink at initial sintering stage with lots of micro pores formed, resulting in inadequate grain rearrangement and mass transfer among grains, which is confirmed to be the reason why samples with nm-TiO₂ powder exhibit the highest

Fig. 2 Comparative SEM of polished sections of ternary system samples



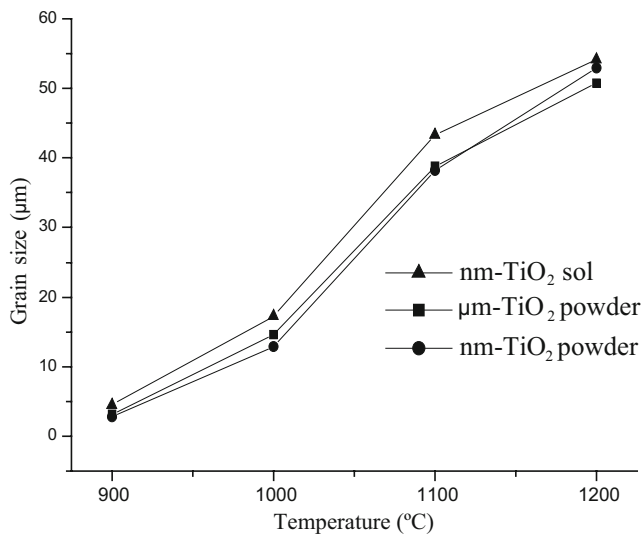


Fig. 3 Variation of grain size with sintering temperature

porosity and small grain sizes at low sintering temperature. Although μm-TiO₂ powder didn't aggregate during sintering, its size was much larger than that of nm-TiO₂ sol, which more or less restricted the effect of TiO₂ on ZnO grain growth and mass transfer. Thus, at 1200 °C, samples added with μm-TiO₂ powder exhibit the smallest grain size.

At 900 °C, as the Eq. 1 described [9],



the reaction between TiO₂ and Bi₂O₃ resulted in lack of Bi₂O₃ liquid phases, which can form Bi-rich boundary. From that, lack of grain boundary in samples added nm-TiO₂ sol can be attribute to high reactivity of nm-TiO₂ sol.

3.2 Electrical properties

The most important electrical properties are breakdown voltage gradient (U_b), nonlinear coefficient (α) and leakage current (I_L). To low voltage varistor, U_b and I_L should be low. As described in Fig. 4, it's found that samples with nm-TiO₂ sol have the lowest U_b , α and I_L .

The relationship between U_b (V/mm), average grain diameter d_0 (μm) and breakdown voltage V_g (V) is given by:

$$U_b = (1000/d_0 - 1)V_g \approx 1000V_g/d_0 \quad (2)$$

According to this equation, the largest grains in samples with nm-TiO₂ sol result in the lowest U_b directly. Variation of

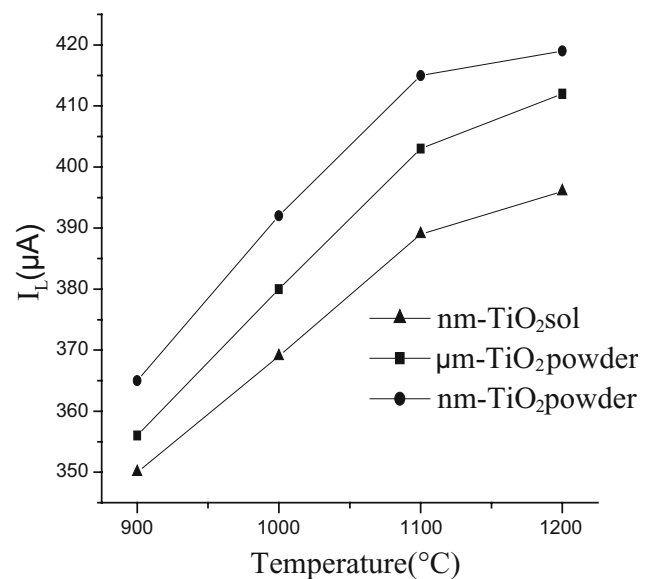
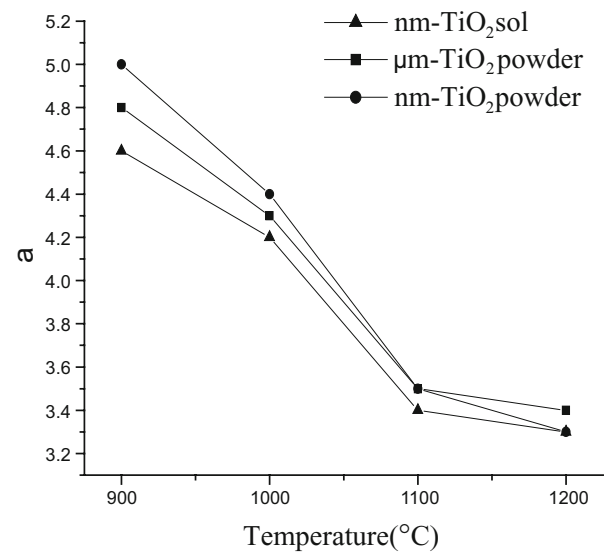
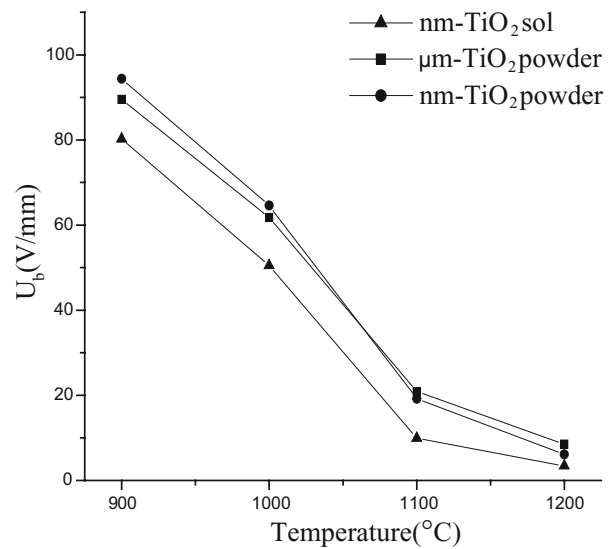


Fig. 4 Variation of electric properties data (U_b , α , I_L) of ternary system samples (ZnO–Bi₂O₃–TiO₂)

U_b is opposite to variation of grain size in combination with Figs. 3 and 4. It can be concluded that nm-TiO₂ sol can lower down breakdown voltage largely (even lower than 3.2V/mm).

In terms of hole induced tunneling theory [10], α results from the tunneling of the boundary barrier and decreases with increasing donor concentration. As previous papers [6] mentioned, replacement diffusion of Ti cations into the lattice sites of Zn cations gives rise to donor concentration. High reactivity of nm-TiO₂ sol provides a considerable contribution to donor concentration. Therefore, α of samples with nm-TiO₂ sol is the lowest, but not much lower than the other two samples.

The current/voltage characteristic of varistors is often empirically described by Power-Law Relation [11],

$$I = (U/C)^\alpha \quad (3)$$

where U is the on-load voltage, C is material constant. From this equation, in the condition of $U < C$, α is in inverse proportion to I_L . But there is an exception in samples with nm-TiO₂ sol that both α and I_L are the lowest, which is in apparent contradiction to Power-Law Relation. While loading DC voltage on the varistor, leakage current I_L is following grain–boundary–grain path mainly, whose value is determined by conductivity of Bi-rich skeleton. From microstructure analysis above, the Bi-rich grain boundaries are very lack in samples added with nm-TiO₂ sol, which result in lack of path for leakage current. Thus, leakage current is the lowest exceptionally.

4 Conclusion

The low voltage varistors added with nm-TiO₂ sol exhibits large density, low porosity, big granular size, low breakdown voltage gradient and small leakage current, hence nm-TiO₂ sol dopant is the best grain growth enhancing additive for optimizing almost all the electrical parameters of low voltage ZnO varistors, except nonlinear coefficient α , which can be improved by other ways.

Nm-TiO₂ powder exists in forms of agglomerates, whose size is even larger than $\mu\text{m-TiO}_2$ powder. As a result, nano-effect of nm-TiO₂ powder cannot bring into play fully as nm-TiO₂ sol.

The size of $\mu\text{m-TiO}_2$ powder is much larger than that of nm-TiO₂, which more or less restricted the effect of TiO₂ on ZnO grain growth and mass transfer. Thus, doping effect of $\mu\text{m-TiO}_2$ is not so well as nm-TiO₂.

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